

Amendments to the Specification

Please replace the paragraph at page 10, line 27 through page 11, line 2 with the following amended paragraph:

Note that the path segment 106 carries all the signals handled ~~be~~ by the device and therefore it will be referred to as "signal path". Note also that within the signal path 106 the direction of polarization of signals passing through QWP or FR 18 is substantially orthogonal to the direction of polarization of signals passing through QWP or FR 14.

Please replace the paragraph at page 13, lines 15 through 25 with the following amended paragraph:

For conventional dielectric narrowband filters, n_{eff} is typically approximately between 1.5 and 1.8. For higher index materials one can obtain values of 3.2 and greater using, for example, III-V semiconductor materials, such as GaAs/AlGaAs or InGaAs/AlAsSb. A plot of the change in center wavelength, $\delta\lambda$, as a function of the angle of incidence is shown in FIG. ~~8~~ 9 for different n_{eff} values. One can use Snell's law to understand that a high index material will bend light more towards the normal than a low index material; this concept extends to the case here, where an effective index describes Fresnel interactions. Such high index narrowband filters provide low angle sensitivity for the wavelength selective reflectors thus allowing different signals' frequencies to be spaced as closely as about 1 nm (about 125 Ghz) and at the same time keeping the field of view as wide as approximately 10 degrees.

Please replace the paragraph at page 16, lines 9 through 10 with the following amended paragraph:

The directional rotation module composed of HWP 223 and FR 224 may take the role of the directional rotation modules 211 and 213 of FIG. ~~12~~ 13.